

Switching diode

1SS380

●Applications

Low leakage switching

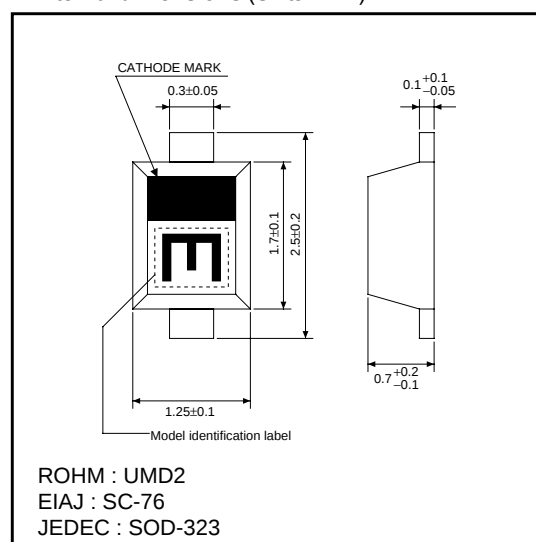
●Features

- 1) Small surface mounting type. (UMD2)
- 2) Ultra low I_R . ($I_R=40\text{pA Typ.}$)
- 3) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	35	V
Peak forward current	I_{FM}	225	mA
Mean rectifying current	I_o	100	mA
Surge current (1s)	I_{surge}	400	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+125	°C

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditons
Forward voltage	V_F	—	—	1.2	V	$I_F=100\text{mA}$
Reverse current	I_R	—	—	10	nA	$V_R=20\text{V}$
Capacitance between terminals	C_T	—	—	5.0	pF	$V_R=0.5\text{V}$, $f=1\text{MHz}$

Diodes

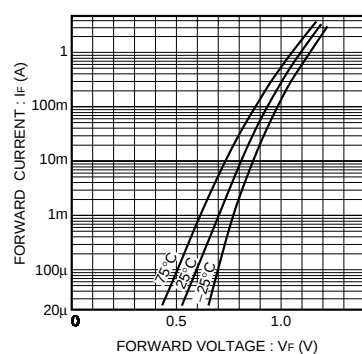
●Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

Fig. 1 Forward characteristics

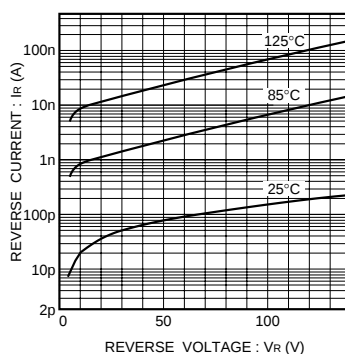


Fig. 2 Reverse characteristics

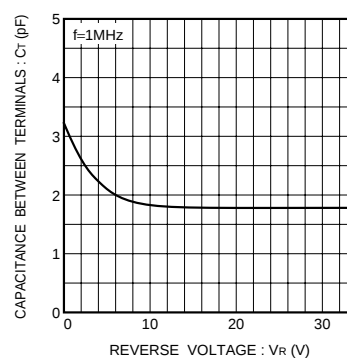


Fig. 3 Capacitance between terminals characteristics

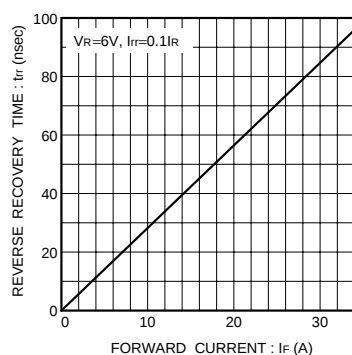


Fig. 4 Reverse recovery time characteristics

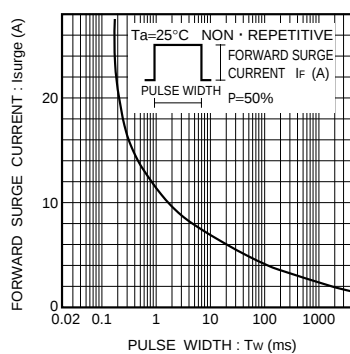
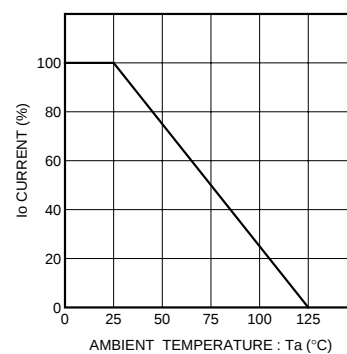


Fig. 5 Surge current characteristics

Fig. 6 Derating curve
(mounting on glass epoxy PCBs)